

2SC2986

SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

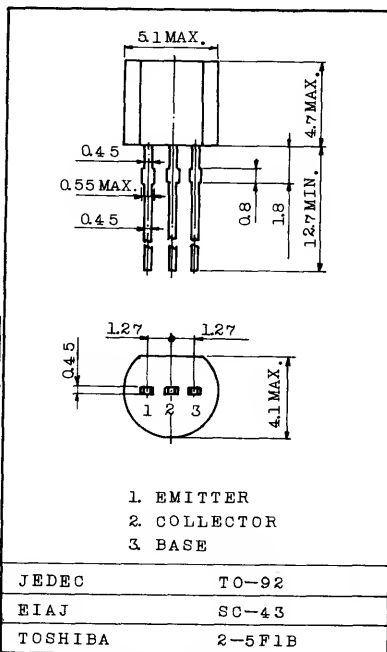
FM/AM, RF, MIX, OSC, IF
HIGH FREQUENCY AMPLIFIER APPLICATIONS.

FEATURES:

- High Stability Oscillation Voltage On FM Local Oscillator.
- Recommend FM/AM RF, MIX, OSC, and IF.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter-Base Voltage	V _{EBO}	4	V
Collector Current	I _C	50	mA
Emitter Current	I _E	-50	mA
Collector Power Dissipation	P _C	300	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	-55 ~ 125	°C

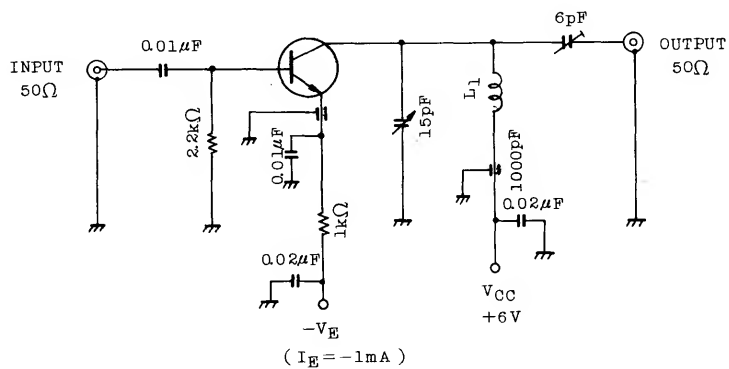


Weight : 0.21g

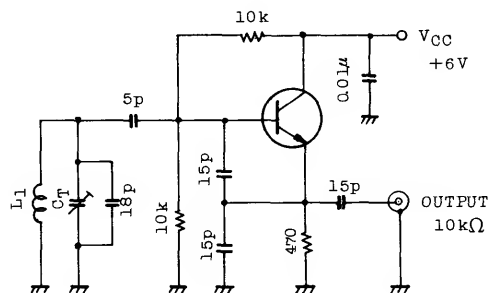
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	V _{CB} =40V, I _E =0	-	-	0.1	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} =4V, I _C =0	-	-	0.5	μA
DC Current Gain	h _{FE} (Note)	V _{CE} =6V, I _C =1mA	40	-	240	
Reverse Transfer Capacitance	C _{re}	V _{CE} =6V, f=1MHz	-	0.9	1.3	pF
Transition Frequency	f _T	V _{CE} =6V, I _E =-1mA	150	350	-	MHz
Collector-Base Time Constant	C _{c.rbb'}	V _{CE} =6V, I _E =-1mA, f=30MHz	-	15	30	ps
Noise Figure	NF	V _{CC} =6V, I _E =-1mA	-	4.0	-	dB
Power Gain	G _{pe}	f=100MHz (Fig.1)	-	15	-	
Oscillation Output Voltage	V _{OSC}	V _{CC} =6V, f=100MHz (Fig.2)	-	150	-	mV

Note : h_{FE} Classification R:40~80 O:70~140 Y:120~240

Fig. 1 NF, G_{pe} TEST CIRCUIT

L_1 : 0.8mm ϕ SILVER PLATED COPPER WIRE, 4T, 10ID, 8 LENGTH

Fig. 2 V_{OSC} TEST CIRCUIT

L_1 : 0.8mm ϕ SILVER PLATED COPPER WIRE, 4T, 10ID, 8 LENGTH

STATIC CHARACTERISTICS

